

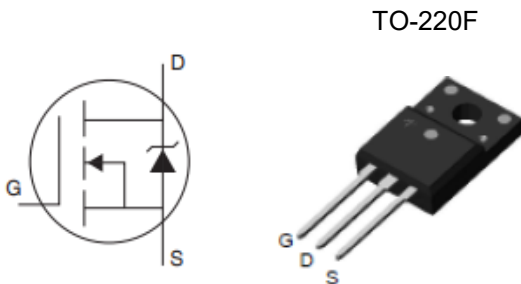
Description

The APM60R180F is the N-Channel enhancement mode power field effect transistors with high cell density, high voltage Super Junction technology. This high density process and design have been optimized switching performance and especially tailored to minimize on-state resistance.

Features

- VDS: 600V
- ID (@VGS=10V): 18A
- RDS_{ON} (@VGS=10V) : < 180mΩ
- High density cell design for extremely low RDS_{ON}
- Excellent on-resistance and DC current capability

Equivalent Circuit and Pin Configuration



Applications

- AC/DC load switch
- SMPS
- LED power

Marking Information



XXXX = Date Code

Ordering Information

P/N	Package Type	Packaging
APM60R180F	TO-220F	Tube

Absolute Maximum Ratings (T_c=25 °C unless otherwise noted)

Parameter	Symbol	Maximum	Unit
Drain-source Voltage	V _{DS}	600	V
Gate-source Voltage	V _{GS}	±30	V
Continuous Drain Current ⁽¹⁾⁽⁴⁾	I _D	T _c =25°C	18
		T _c =100°C	11.5
Pulsed Drain Current ⁽²⁾	I _{DM}	54.6	A
Total Power Dissipation ⁽³⁾	P _d @ T _c =25°C	125	W
	Derating Factor above 25°C	1.00	W/°C
Thermal Resistance Junction-to-Case ⁽³⁾	R _{θJC}	1	°C/W
Junction and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (T_c=25 °C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	B _V D _{SS}	V _{GS} =0V, I _D =250μA	600			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V, T _C =25°C			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source on-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =10.5A		140	180	mΩ
Diode Forward Voltage	V _{SD}	I _S =18A, V _{GS} =0V			1.4	V
Maximum Body-Diode Continuous Current	I _S				18	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =100V, V _{GS} =0V, f=1MHz		1550		pF
Output Capacitance	C _{oss}			67		
Reverse Transfer Capacitance	C _{rss}			1.5		
Switching Parameters						
Total Gate Charge	Q _g	V _{DS} =480V, I _D =10.5A, V _{GS} =10V		38		nC
Gate Source Charge	Q _{gs}			6.6		
Gate Drain Charge	Q _{gd}			15.2		
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =60V, I _D =4A, R _{GEN} =25Ω		48		ns
Turn-on Rise Time	t _r			57		
Turn-off Delay Time	t _{D(off)}			80		
Turn-off Fall Time	t _f			48		

Noted: (1) Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%

(2) Pulse width limited by maximum junction temperature

(3) Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. With 2oz Copper, t ≤ 10s

(4) Drain current limited by maximum junction temperature

Typical Performance Characteristics

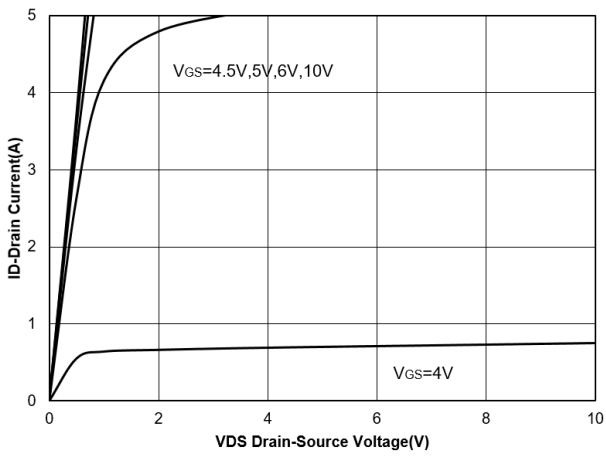


Figure 1. Output Characteristics

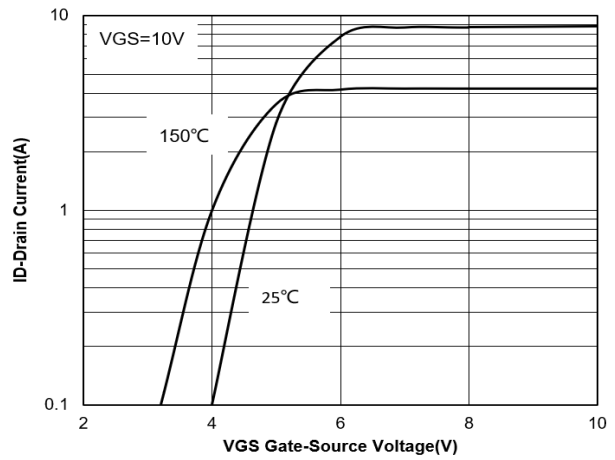


Figure 2. Transfer Characteristics

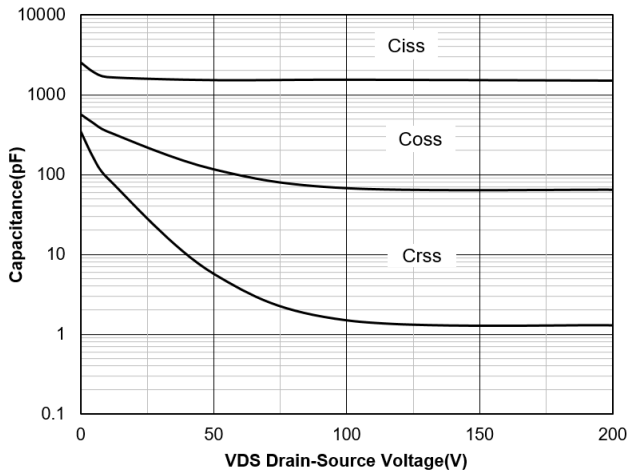


Figure 3. Capacitance Characteristics

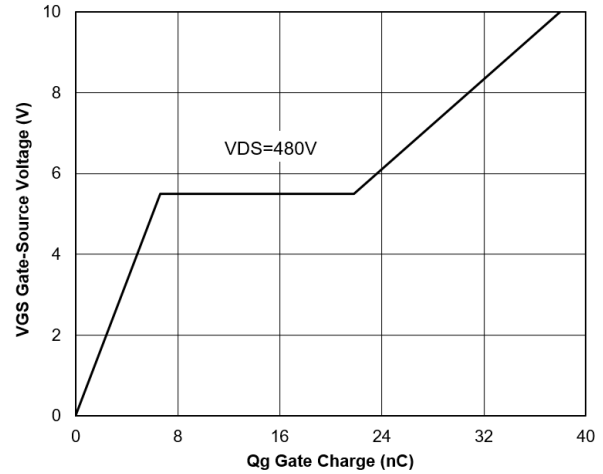


Figure 4. Gate Charge

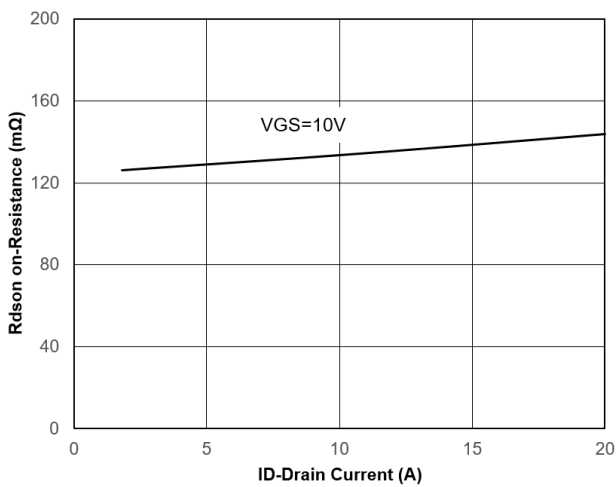


Figure 5. Drain-Source on Resistance

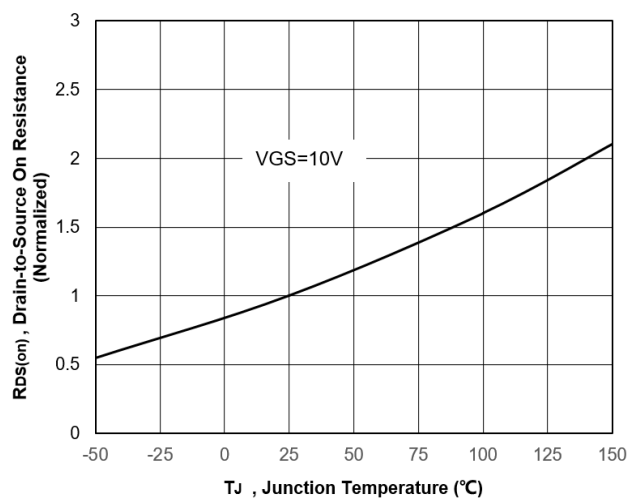


Figure 6. Normalized On-Resistance Vs. Temperature

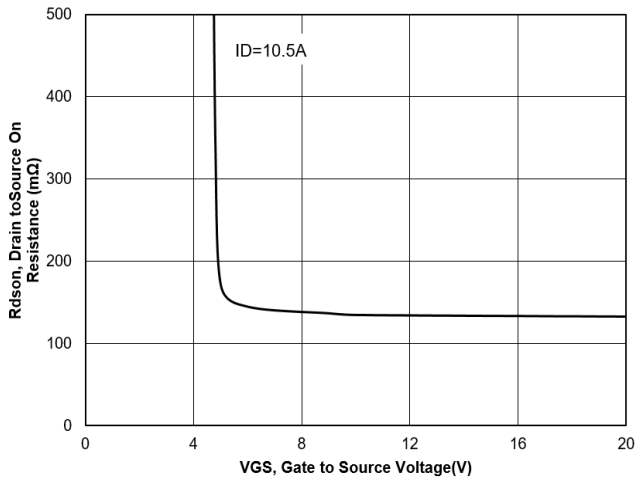


Figure 7. Typical Drain to Source ON Resistance VS Gate Voltage and Drain Current

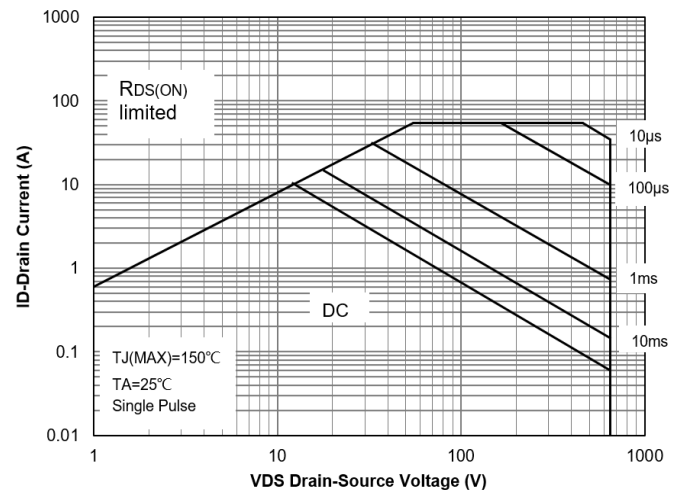


Figure 8. Safe Operation Area

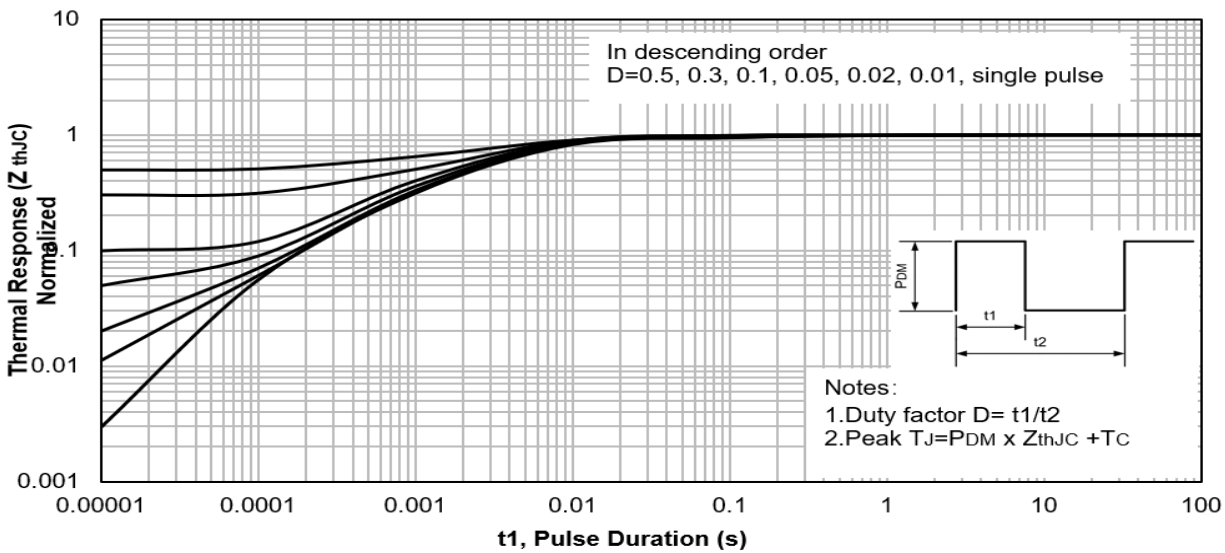


Figure 9. Maximum Effective Transient Thermal Impedance ,Junction-to-Case

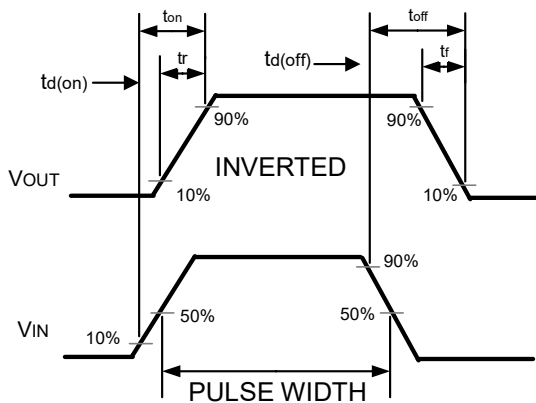
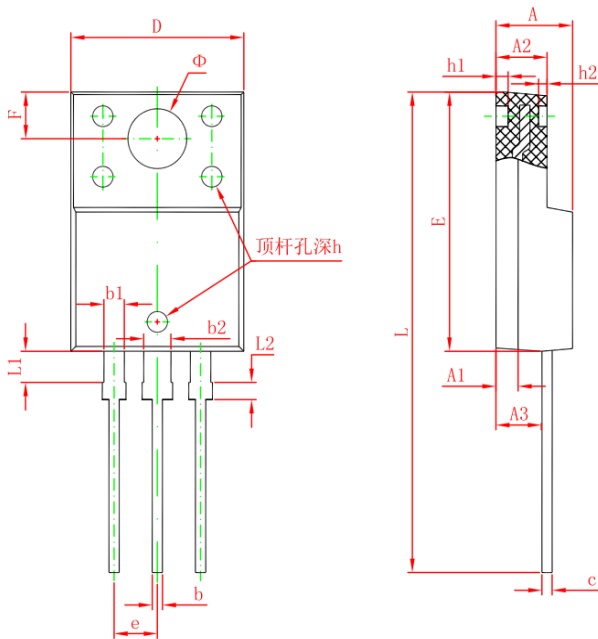


Figure 10. Switching wave

TO-220F Package Outline Drawing



Symbol	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	1.300 REF.		0.051 REF.	
A2	2.800	3.200	0.110	0.126
A3	2.500	2.900	0.098	0.114
b	0.500	0.750	0.020	0.030
b1	1.100	1.350	0.043	0.053
b2	1.500	1.750	0.059	0.069
c	0.500	0.750	0.020	0.030
D	9.960	10.360	0.392	0.408
E	14.800	15.200	0.583	0.598
e	2.540 TYP.		0.100 TYP.	
F	2.700 REF.		0.106 REF.	
Φ	3.500 REF.		0.138 REF.	
h	0.000	0.300	0.000	0.012
h1	0.800 REF.		0.031 REF.	
h2	0.500 REF.		0.020 REF.	
L	28.000	28.400	1.102	1.118
L1	1.700	1.900	0.067	0.075
L2	0.900	1.100	0.035	0.043

Contact Information

Applied Power Microelectronics Inc.

Website: <http://www.appliedpowermicro.com>

Email: sales@appliedpowermicro.com

Phone: +86 (0519) 8399 3606